



Docket No.: M4065.0051/P051-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Leonard Forbes, et al.

Application No.: 09/609,813

Filed: July 3, 2000

Group Art Unit: 2815

Examiner: P. Brock, II

For: HIGH DENSITY PLANAR SRAM CELL  
USING BIPOLAR LATCHUP AND GATED  
DIODE BREAKDOWN

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**REQUEST FOR RECONSIDERATION  
AND AMENDMENT UNDER 37 C.F.R. § 1.116**

09/24/2002 JHEXILLA 00000003 041073 09609813  
01 FC:115 110.00 CH  
Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington, DC 20231

Dear Sir:

In response to the Office Action dated May 13, 2002 (Paper No. 17), please  
amend the above-identified U.S. Patent application as follows:

**In the Claims:**

**Please rewrite claims 48 and 55 as follows:**

48. (Thrice Amended) A method of forming a circuit for storing information as  
one of at least two possible stable current states, the method comprising the following  
steps:

providing a semiconductor substrate;

providing doped silicon regions to form a multi-region planar thyristor having at